Vishay Semiconductors

Small Signal Schottky Diodes

Features

- Integrated protection ring against static discharge
- Low capacitance
- Low leakage current
- Low forward voltage drop
- Lead (Pb)-free component
- Component in accordance to RoHS 2002/95/EC and WEEE 2002/96/EC

Applications

- HF-Detector
- Protection circuit
- Small battery charger
- AC-DC/DC-DC converters

Mechanical Data

Case: MiniMELF Glass case SOD80 Weight: approx. 31 mg Cathode Band Color: black Packaging Codes/Options:

GS18/10 k per 13" reel (8 mm tape), 10 k/box

GS08/2.5 k per 7" reel (8 mm tape), 12.5 k/box

Parts Table

Part	Type differentiation	Ordering code	Type Marking	Remarks	
LL103A	$V_{R} = 40$ V, V_{F} at $I_{F} = 20$ mA max. 370 mV	LL103A-GS08 or LL103A-GS18	-	Tape and Reel	
LL103B	V_{R} = 30 V, V_{F} at I_{F} = 20 mA max. 370 mV	LL103B-GS08 or LL103B-GS18	-	Tape and Reel	
LL103C	V_{R} = 20 V, V_{F} at I_{F} = 20 mA max. 370 mV	LL103C-GS08 or LL103C-GS18	-	Tape and Reel	

Absolute Maximum Ratings

 $T_{amb} = 25$ °C, unless otherwise specified

Parameter	Test condition	Part	Symbol	Value	Unit	
Reverse voltage		LL103A	V _R	40	V	
		LL103B	V _R	30	V	
		LL103C	V _R	20	V	
Forward continuous current			I _{FAV}	200	mA	
Peak forward surge current	$t_p = 300 \ \mu s$, square pulse		I _{FSM}	15	A	
Power dissipation	$I = 4 \text{ mm}, T_L = \text{constant}$		P _{tot}	400	mW	

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Thermal Characteristics

T_{amb} = 25 °C, unless otherwise specified

Parameter	Test condition	Symbol	Value	Unit	
Thermal resistance junction to ambient air	$I = 4 \text{ mm}, T_L = \text{constant}$	R _{thJA}	250	K/W	
Junction temperature		Тj	125	°C	
Storage temperature range		T _{stg}	- 65 to + 150	°C	

Electrical Characteristics

 T_{amb} = 25 °C, unless otherwise specified

Parameter	Test condition	Part	Symbol	Min	Тур.	Max	Unit
Reverse breakdown voltage	I _R = 50 μA	LL103A	V _(BR)	40			V
		LL103B	V _(BR)	30			V
		LL103C	V _(BR)	20			V
Leakage current	V _R = 30 V	LL103A	I _R			5	μΑ
	V _R = 20 V	LL103B	I _R			5	μΑ
	V _R = 10 V	LL103C	I _R			5	μA
Forward voltage drop	I _F = 20 mA		V _F			370	mV
	I _F = 200 mA		V _F			600	mV
Diode capacitance	V _R = 0 V, f = 1 MHz		CD		50		pF
Reverse recovery time	$I_F = I_R = 50$ to 200 mA, recover to 0.1 I_R		t _{rr}		10		ns

Typical Characteristics

 T_{amb} = 25 °C, unless otherwise specified

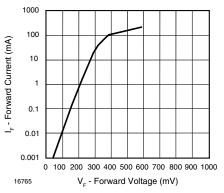


Figure 1. Forward Current vs. Forward Voltage

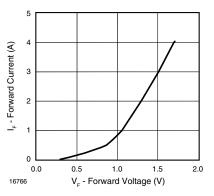


Figure 2. Forward Current vs. Forward Voltage



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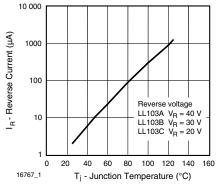


Figure 3. Reverse Current vs. Junction Temperature

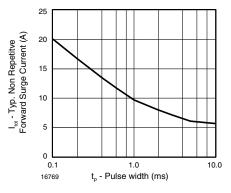


Figure 5. Typ. Non Repetitive Forward Surge Current vs. Pulse width

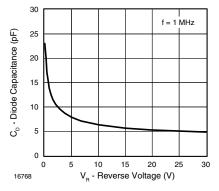
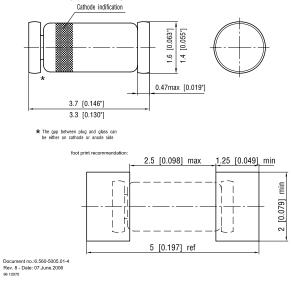


Figure 4. Diode Capacitance vs. Reverse Voltage

Package Dimensions in mm (Inches): SOD80



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Ozone Depleting Substances Policy Statement

It is the policy of Vishay Semiconductor GmbH to

- 1. Meet all present and future national and international statutory requirements.
- 2. Regularly and continuously improve the performance of our products, processes, distribution and operating systems with respect to their impact on the health and safety of our employees and the public, as well as their impact on the environment.

It is particular concern to control or eliminate releases of those substances into the atmosphere which are known as ozone depleting substances (ODSs).

The Montreal Protocol (1987) and its London Amendments (1990) intend to severely restrict the use of ODSs and forbid their use within the next ten years. Various national and international initiatives are pressing for an earlier ban on these substances.

Vishay Semiconductor GmbH has been able to use its policy of continuous improvements to eliminate the use of ODSs listed in the following documents.

- 1. Annex A, B and list of transitional substances of the Montreal Protocol and the London Amendments respectively
- 2. Class I and II ozone depleting substances in the Clean Air Act Amendments of 1990 by the Environmental Protection Agency (EPA) in the USA
- 3. Council Decision 88/540/EEC and 91/690/EEC Annex A, B and C (transitional substances) respectively.

Vishay Semiconductor GmbH can certify that our semiconductors are not manufactured with ozone depleting substances and do not contain such substances.

We reserve the right to make changes to improve technical design and may do so without further notice.

Parameters can vary in different applications. All operating parameters must be validated for each customer application by the customer. Should the buyer use Vishay Semiconductors products for any unintended or unauthorized application, the buyer shall indemnify Vishay Semiconductors against all claims, costs, damages, and expenses, arising out of, directly or indirectly, any claim of personal damage, injury or death associated with such unintended or unauthorized use.

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